

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (π -MOS VI)

2SK4107

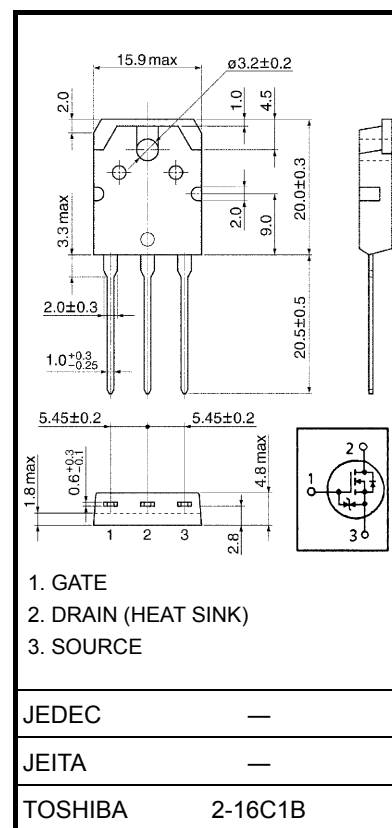
○ Switching Regulator Applications

Unit: mm

- Low drain-source ON resistance : $R_{DS(ON)} = 0.33 \Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 8.5 S$ (typ.)
- Low leakage current : $I_{DSS} = 100 \mu A$ (max) ($V_{DS} = 500 V$)
- Enhancement mode : $V_{th} = 2.0 \sim 4.0 V$ ($V_{DS} = 10 V$, $I_D = 1 mA$)

Absolute Maximum Ratings ($T_a = 25^\circ C$)

| Characteristic | | Symbol | Rating | Unit |
|--|----------------|-----------|----------------|------------|
| Drain-source voltage | | V_{DSS} | 500 | V |
| Drain-gate voltage ($R_{GS} = 20 k\Omega$) | | V_{DGR} | 500 | V |
| Gate-source voltage | | V_{GSS} | ± 30 | V |
| Drain current | DC (Note 1) | I_D | 15 | A |
| | Pulse (Note 1) | I_{DP} | 60 | A |
| Drain power dissipation ($T_c = 25^\circ C$) | | P_D | 150 | W |
| Single-pulse avalanche energy (Note 2) | | E_{AS} | 765 | mJ |
| Avalanche current | | I_{AR} | 15 | A |
| Repetitive avalanche energy (Note 3) | | E_{AR} | 15 | mJ |
| Channel temperature | | T_{ch} | 150 | $^\circ C$ |
| Storage temperature range | | T_{stg} | $-55 \sim 150$ | $^\circ C$ |



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

| Characteristic | Symbol | Max | Unit |
|--|----------------|-------|--------------|
| Thermal resistance, channel to case | $R_{th(ch-c)}$ | 0.833 | $^\circ C/W$ |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 50 | $^\circ C/W$ |

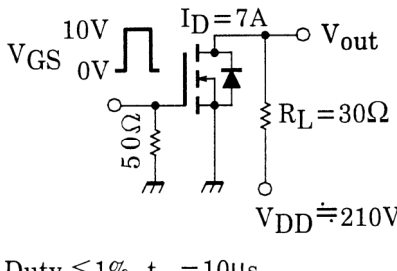
Note 1: Ensure that the channel temperature does not exceed $150^\circ C$.

Note 2: $V_{DD} = 90 V$, $T_{ch} = 25^\circ C$ (initial), $L = 5.78 mH$, $R_G = 25 \Omega$, $I_{AR} = 15 A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

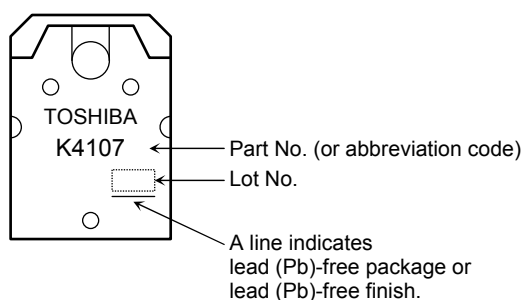
Electrical Characteristics (Ta = 25°C)

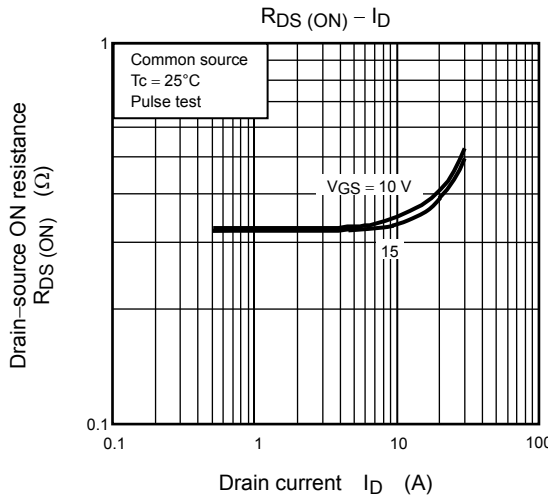
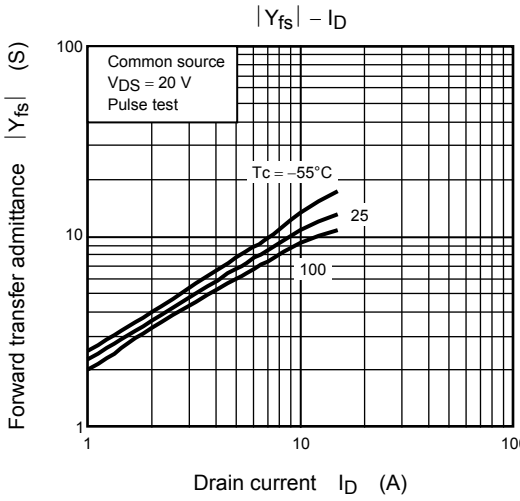
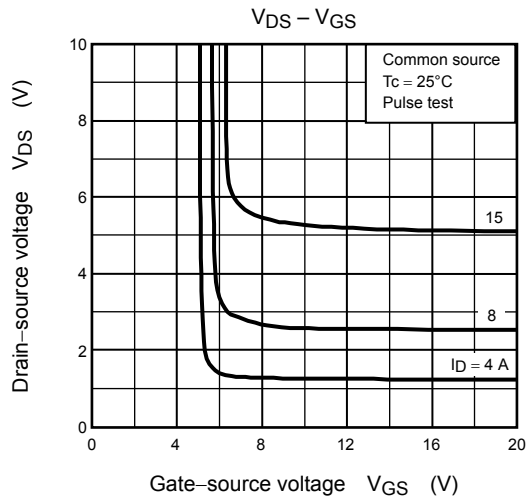
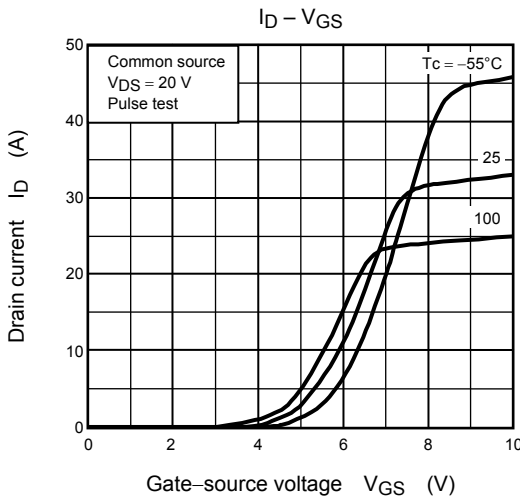
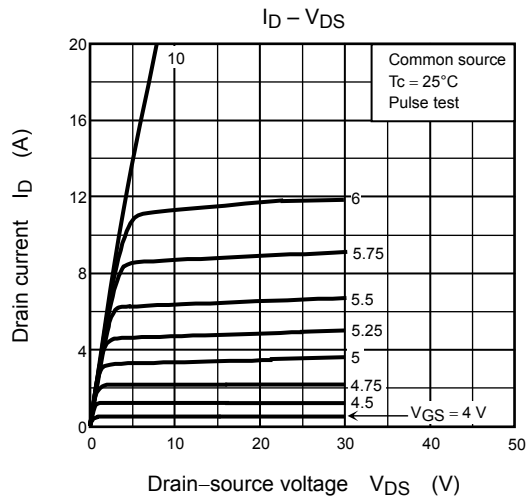
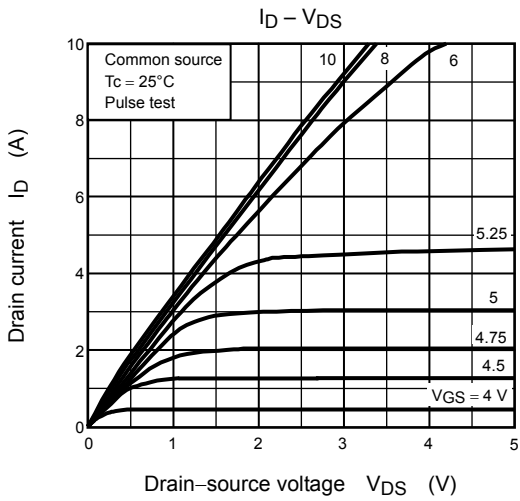
| Characteristic | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---------------|----------------|--|----------|------|----------|---------------|
| Gate leakage current | | I_{GSS} | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$ | — | — | ± 10 | μA |
| Gate-source breakdown voltage | | $V_{(BR) GSS}$ | $I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$ | ± 30 | — | — | V |
| Drain cutoff current | | I_{DSS} | $V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$ | — | — | 100 | μA |
| Drain-source breakdown voltage | | $V_{(BR) DSS}$ | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$ | 500 | — | — | V |
| Gate threshold voltage | | V_{th} | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$ | 2.0 | — | 4.0 | V |
| Drain-source ON resistance | | $R_{DS(ON)}$ | $V_{GS} = 10 \text{ V}, I_D = 7.0 \text{ A}$ | — | 0.33 | 0.4 | Ω |
| Forward transfer admittance | | $ Y_{fs} $ | $V_{DS} = 10 \text{ V}, I_D = 7.0 \text{ A}$ | 4.0 | 8.5 | — | S |
| Input capacitance | | C_{iss} | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | — | 2450 | — | pF |
| Reverse transfer capacitance | | C_{rss} | | — | 15 | — | |
| Output capacitance | | C_{oss} | | — | 220 | — | |
| Switching time | Rise time | t_r |  | — | 50 | — | ns |
| | Turn-on time | t_{on} | | — | 90 | — | |
| | Fall time | t_f | | — | 45 | — | |
| | Turn-off time | t_{off} | | — | 175 | — | |
| Total gate charge (gate-source plus gate-drain) | | Q_g | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$ | — | 48 | — | nC |
| Gate-source charge | | Q_{gs} | | — | 26 | — | |
| Gate-drain ("Miller") charge | | Q_{gd} | | — | 22 | — | |

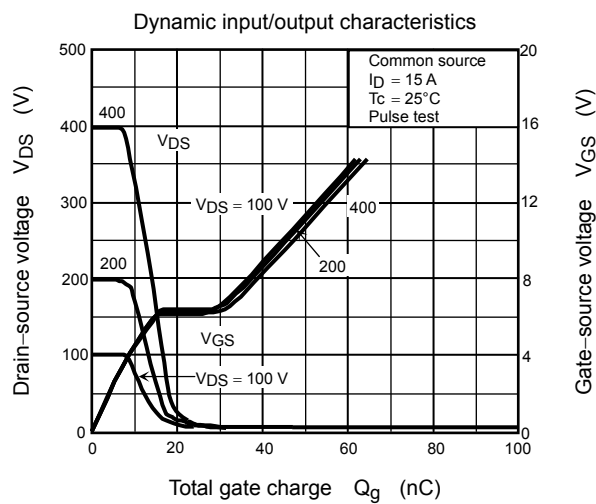
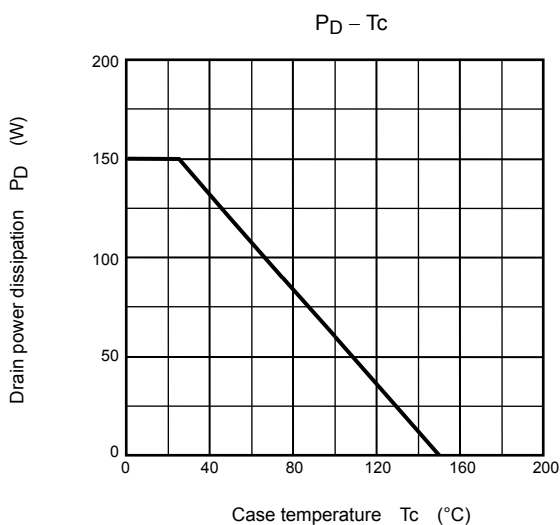
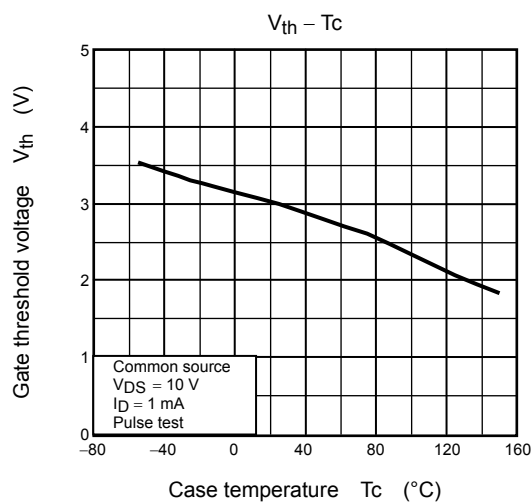
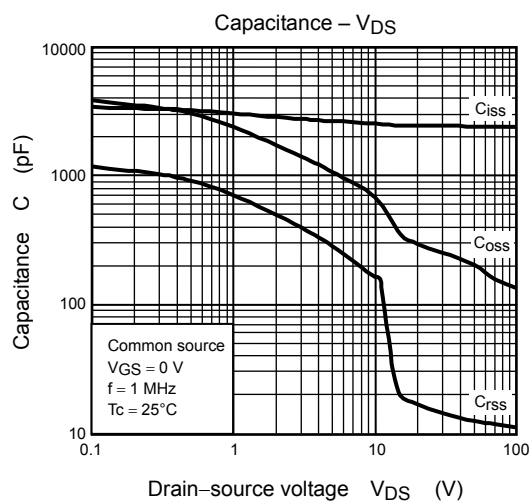
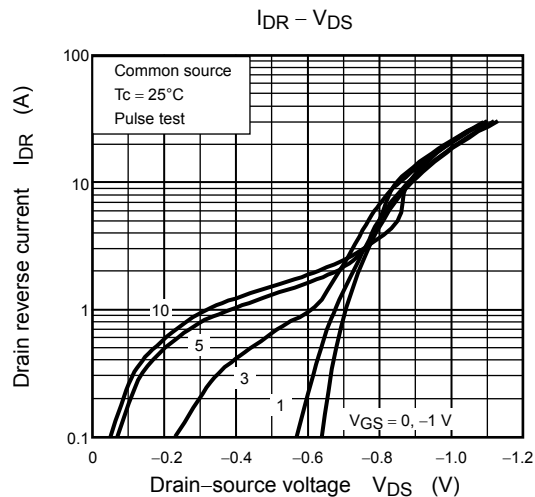
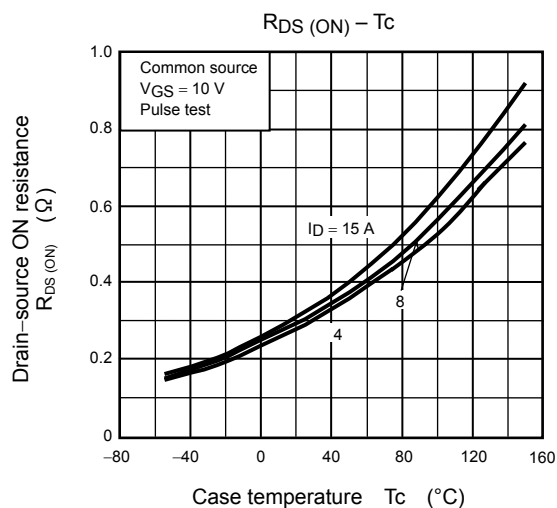
Source-Drain Ratings and Characteristics (Ta = 25°C)

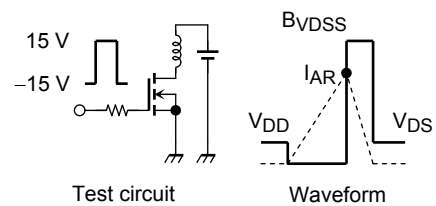
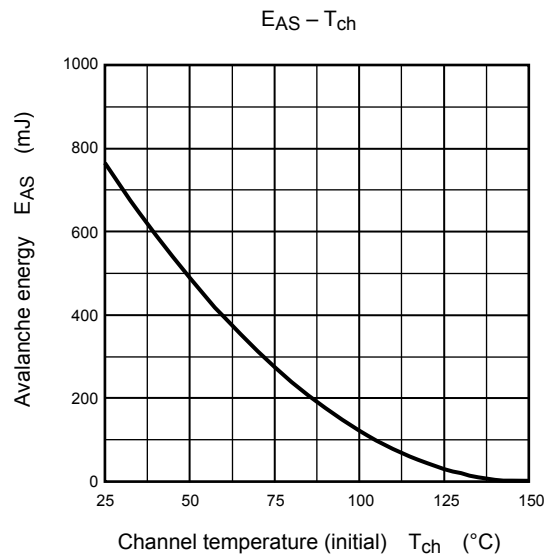
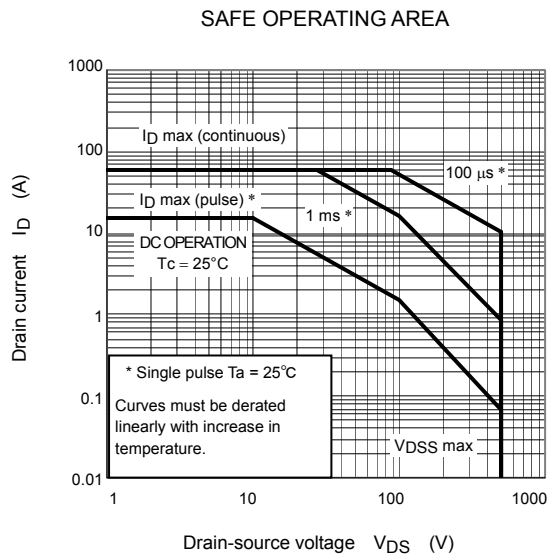
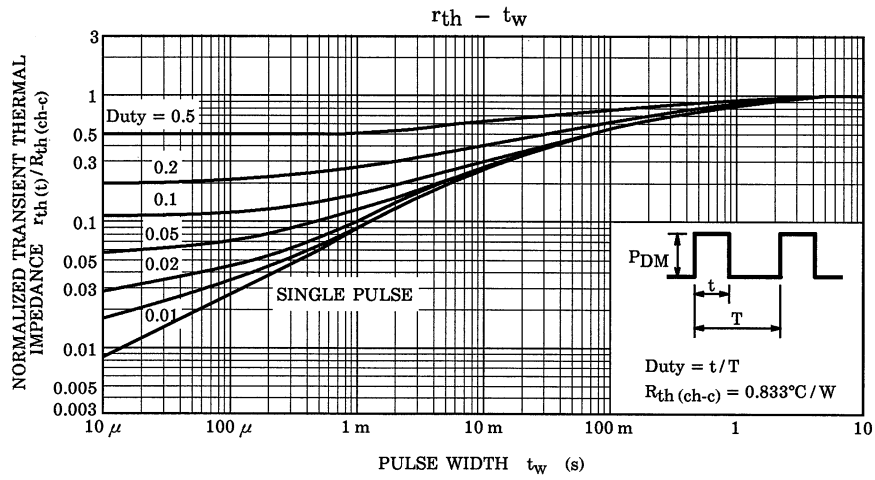
| Characteristic | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|-----------|---|-----|------|------|---------------|
| Continuous drain reverse current (Note 1) | I_{DR} | — | — | — | 15 | A |
| Pulse drain reverse current (Note 1) | I_{DRP} | — | — | — | 60 | A |
| Forward voltage (diode) | V_{DSF} | $I_{DR} = 15 \text{ A}, V_{GS} = 0 \text{ V}$ | — | — | -1.7 | V |
| Reverse recovery time | t_{rr} | $I_{DR} = 15 \text{ A}, V_{GS} = 0 \text{ V}$ | — | 1050 | — | ns |
| Reverse recovery charge | Q_{rr} | $dI_{DR} / dt = 100 \text{ A} / \mu\text{s}$ | — | 13 | — | μC |

Marking









$$R_G = 25 \, \Omega$$

$$V_{DD} = 90 \, \text{V}, L = 5.78 \, \text{mH}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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